DATA SHEET

MOS FIELD EFFECT TRANSISTOR
μPA2550

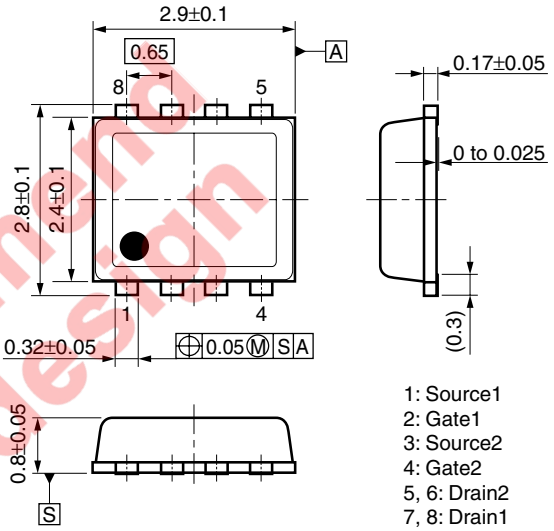
DUAL P-CHANNEL MOSFET FOR SWITCHING

DESCRIPTION

The μPA2550 is dual P-channel MOSFETs designed for power management applications of portable equipments, such as load switch.

Dual P-channel MOSFETs are assembled in one package, to contribute minimize the equipments.

PACKAGE DRAWING (Unit: mm)



1: Source1
2: Gate1
3: Source2
4: Gate2
5, 6: Drain2
7, 8: Drain1

FEATURES

- 1.8 V drive available
- Low on-state resistance
  - $R_{DS(on)1}$ = 40 mΩ MAX. (V_{GS} = –4.5 V, I_D = –2.5 A)
  - $R_{DS(on)2}$ = 60 mΩ MAX. (V_{GS} = –2.5 V, I_D = –2.5 A)
  - $R_{DS(on)3}$ = 93 mΩ MAX. (V_{GS} = –1.8 V, I_D = –2.5 A)
- Built-in gate protection diode
- Small and surface mount package (8-pin VSOF (2429))

ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
μPA2550T1H-T1-AT Note	Pure Sn	8 mm embossed taping 3000 p/reel	8-pin VSOF (2429)
μPA2550T1H-T2-AT Note			

Note Pb-free (This product does not contain Pb in the external electrode and other parts.)

Marking: 2550

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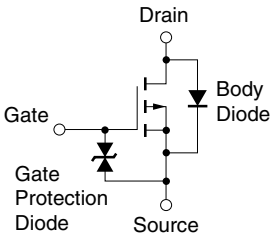
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	−12	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	∓8	V
Drain Current (DC)	$I_{D(DC)}$	∓5.0	A
Drain Current (pulse) Note1	$I_{D(pulse)}$	∓20	A
Total Power Dissipation (1 unit, 5 s) Note2	P_{T1}	1.5	W
Total Power Dissipation (2 units, 5 s) Note2	P_{T2}	2.2	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	−55 to +150	°C

Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Mounted on FR-4 board of 25.4 mm x 25.4 mm x 0.8 mmt

EQUIVALENT CIRCUIT (1/2)



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

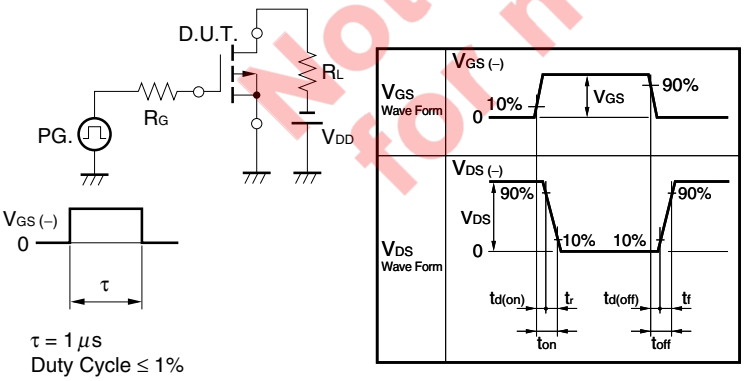
Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –12 V, V_{GS} = 0 V			–1	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ∓8 V, V_{DS} = 0 V			∓10	μA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	V_{DS} = –10 V, I_D = –1 mA	–0.4	–0.7	–1.0	V
Forward Transfer Admittance Note	$\|y_{fs}\|$	V_{DS} = –10 V, I_D = –2.5 A	3.5			S
Drain to Source On-state Resistance Note	$R_{DS(on)1}$	V_{GS} = –4.5 V, I_D = –2.5 A		29	40	mΩ
	$R_{DS(on)2}$	V_{GS} = –2.5 V, I_D = –2.5 A		37	60	mΩ
	$R_{DS(on)3}$	V_{GS} = –1.8 V, I_D = –2.5 A		53	93	mΩ
Input Capacitance	C_{iss}	V_{DS} = –10 V,		930		pF
Output Capacitance	C_{oss}	V_{GS} = 0 V,		200		pF
Reverse Transfer Capacitance	C_{rss}	f = 1.0 MHz		170		pF
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = –6 V, I_D = –2.5 A,		11		ns
Rise Time	t_r	V_{GS} = –4 V,		3.3		ns
Turn-off Delay Time	$t_{d(off)}$	R_G = 6 Ω		70		ns
Fall Time	t_f			46		ns
Total Gate Charge	Q_G	V_{DD} = –6 V, V_{GS} = –4 V, I_D = –5 A		8.7		nC
Body Diode Forward Voltage Note	$V_{F(S-D)}$	I_F = –5 A, V_{GS} = 0 V		0.9		V

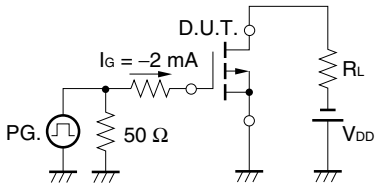
Note Pulsed

TEST CIRCUIT 1 SWITCHING TIME



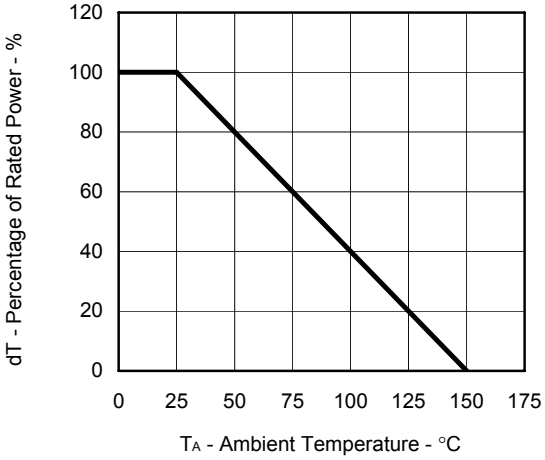
τ = 1 μs
Duty Cycle ≤ 1%

TEST CIRCUIT 2 GATE CHARGE

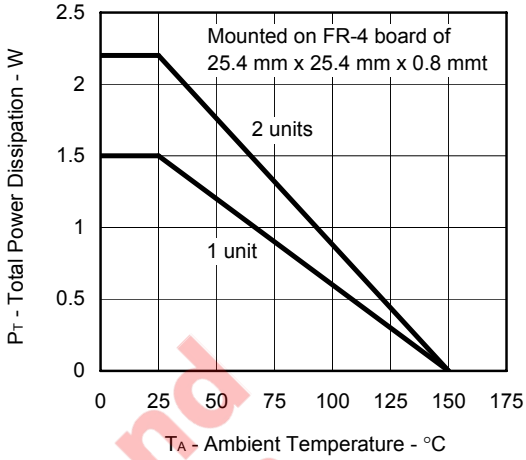


TYPICAL CHARACTERISTICS (T_A = 25°C)

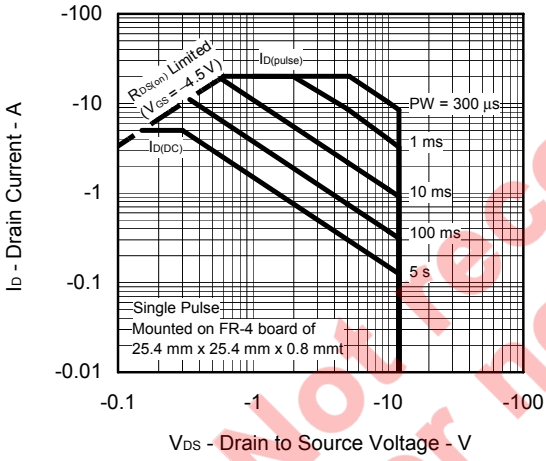
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



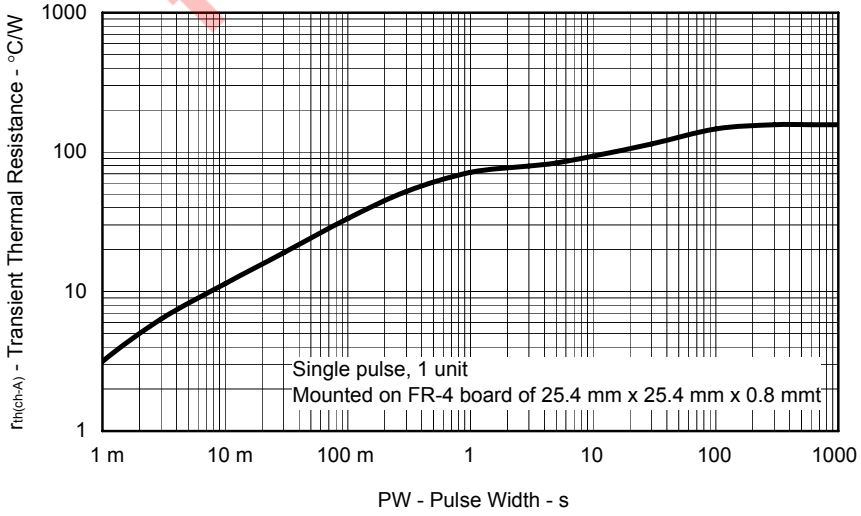
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



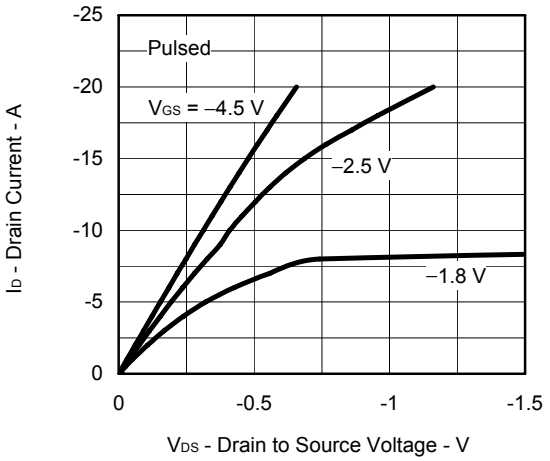
FORWARD BIAS SAFE OPERATING AREA



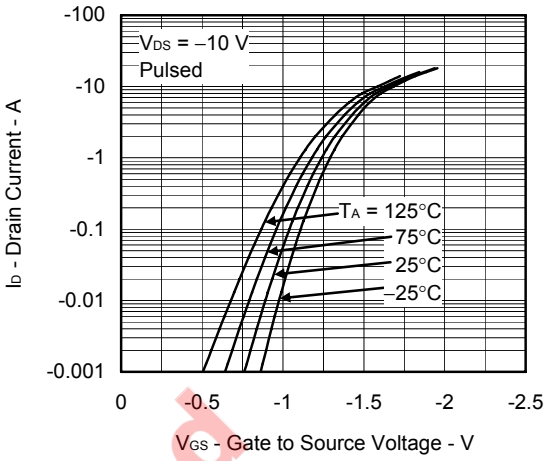
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



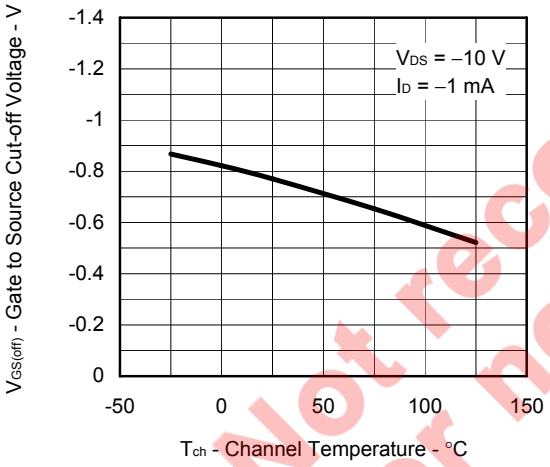
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



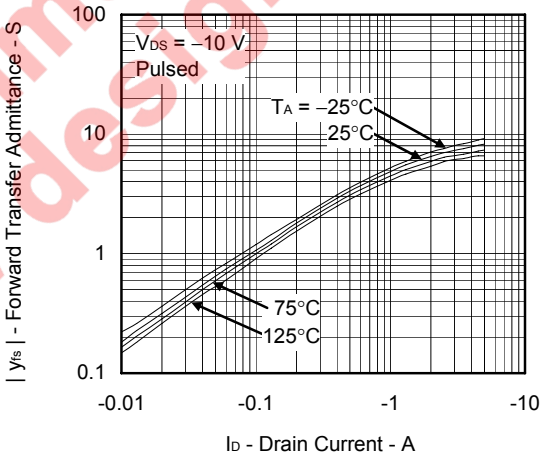
FORWARD TRANSFER CHARACTERISTICS



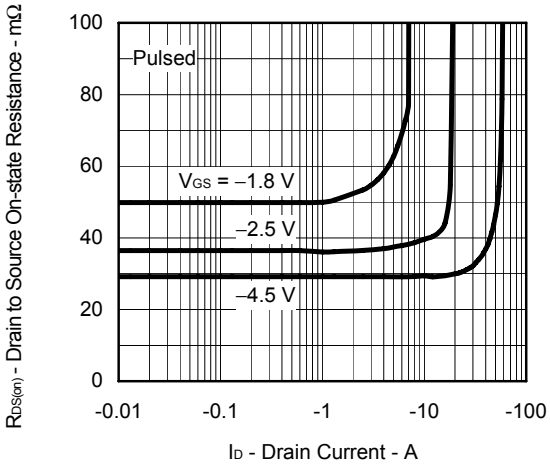
GATE TO SOURCE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATURE



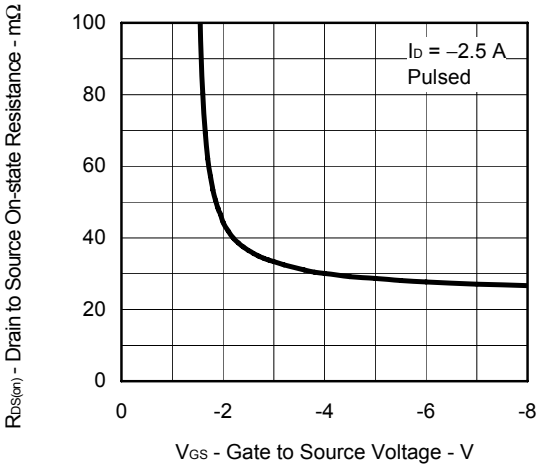
FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT



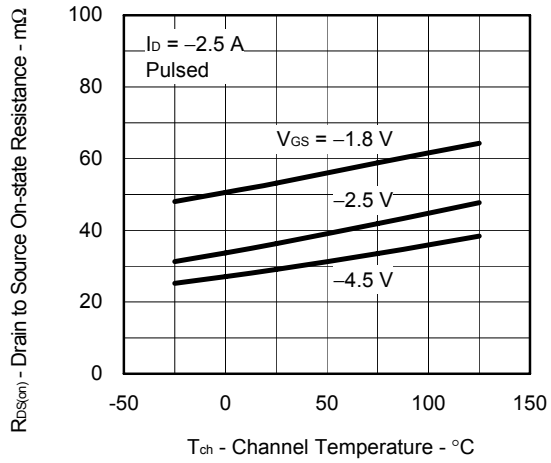
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT



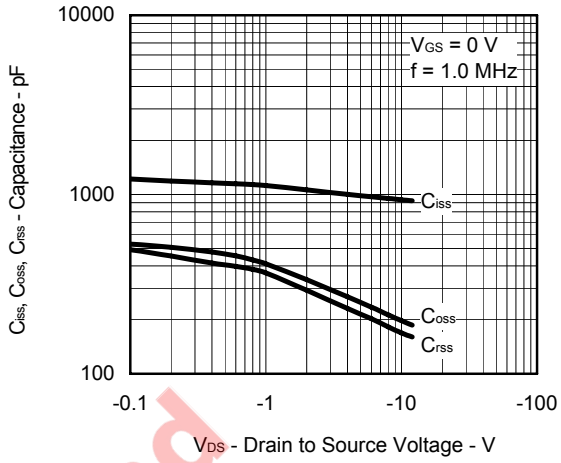
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE



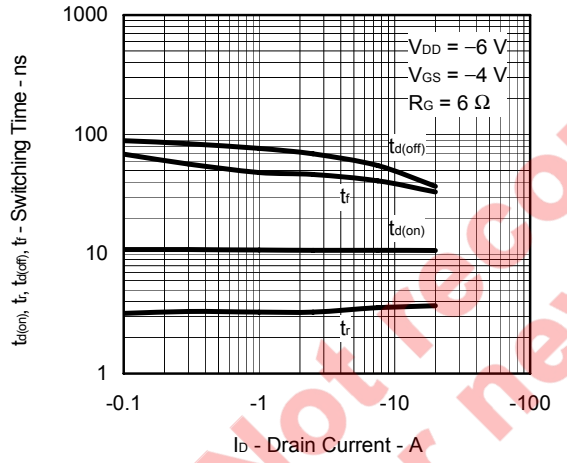
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



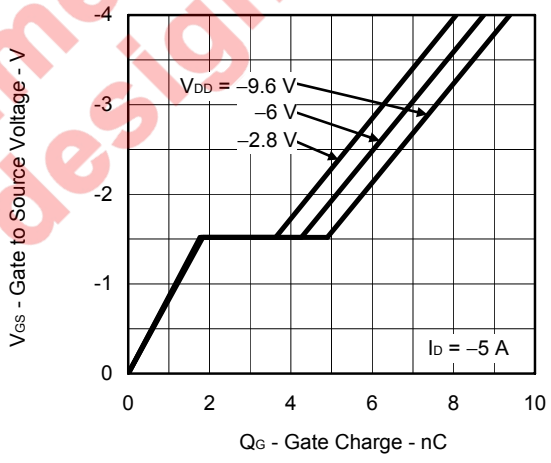
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SWITCHING CHARACTERISTICS



DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE